

November 2014

FPF3040 IntelliMAX[™] 18 V-Rated Dual Input Single Output Power-Source-Selector Switch

Features

- Dual-Input, Single-Output Load Switch
- Input Supply Operating Range:
 - 4~10.5 V at V_{IN}
 - 4~6.5 V at V_{BUS}
- Typical R_{ON}:
 - = 95 m Ω at V_{IN}=5 V
 - 70 mΩ at V_{BUS}=5 V
- Bi-Directional Switch for V_{IN} and V_{BUS}
- Slew Rate Controlled:
 - 50 μ s at V_{IN} for < 4.7 μ F C_{OUT}
 - 90 μ s at V_{BUS} for < 4.7 μ F C_{OUT}
- Maximum I_{sw}: 2 A Per Channel
- Break-Before-Make Transition
- Under-Voltage Lockout (UVLO)
- Over-Voltage Lockout (OVLO)
- Thermal Shutdown
- Logic CMOS IO Meets JESD76 Standard for GPIO Interface and Related Power Supply Requirements
- ESD Protected:
 - Human Body Model: >3 kV
 - Charged Device Model: >1.5 kV
 - IEC 61000-4-2 Air Discharge: >15 kV
 - IEC61000-4-2 Contact Discharge: >8 kV

Description

The FPF3040 is a 18 V-rated Dual-Input Single-Output (DISO) load switch consisting of two channels of slew-rate-controlled, low-on-resistance, N-channel MOSFET switches with protection features. The slew-rate-controlled turn-on characteristic prevents inrush current and the resulting excessive voltage droop on the input power rails. The input voltage range operates from 4 V to 6.5 V at V_{BUS} and from 4 V to 10.5 V at V_{IN} to align with the needs of low-voltage portable device power rails.

 $V_{\rm IN}$ and V_{BUS} have the over-voltage protection functionality of typical 12 V and 7.5 V, respectively, to avoid unwanted damage to system.

 V_{IN} and V_{BUS} bi-directional switching allows reverse current from V_{OUT} to V_{IN} or V_{BUS} for On-The-Go, (OTG) Mode. The switching is controlled by logic input EN and V_{IN_SEL} is capable of interfacing directly with low-voltage control signal General-Purpose Input / Output (GPIO).

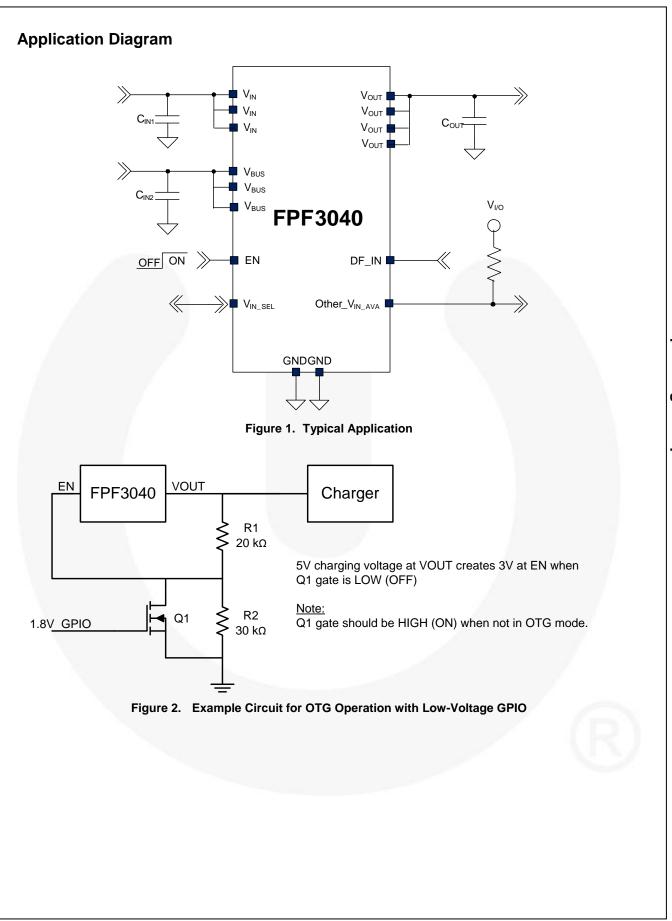
FPF3040 is available in 1.8 mm x 2.0 mm Wafer-Level Chip-Scale Package (WLCSP), 16-bump, 0.4 mm pitch.

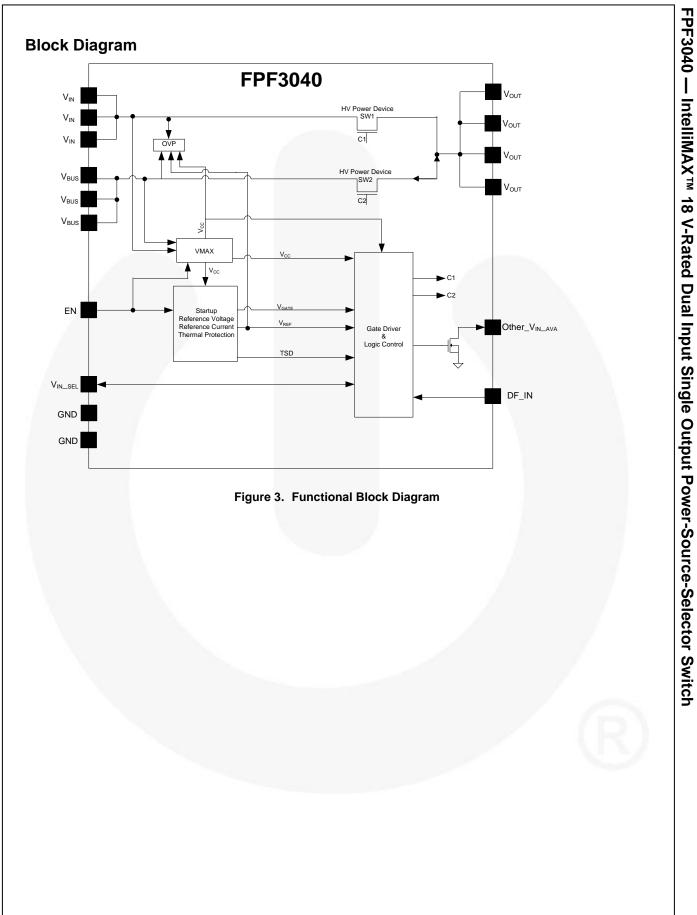
Applications

- Input Power Selection Block Supporting USB and Wireless Charging
- Smartphone / Tablet PC

Ordering Information

Part Number	Top Mark	Channel	Typical R _{ON} per Channel at 5V _{IN}	Rise Time (t _R)	Package
FPF3040UCX	QY	DISO	95 m Ω for V_{IN}	50 μs for V_{IN}	1.8 mm x 2.0 mm Wafer-Level Chip-Scale
FFF30400CX	QT	0130	70 m Ω for V_{BUS}	90 μs for V_{BUS}	Package (WLCSP), 16-Bump, 0.4 mm Pitch





Pin Configuration

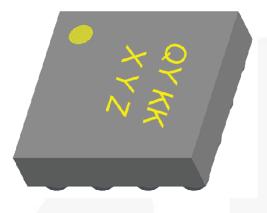


Figure 4. Pin Assignment (Top View)

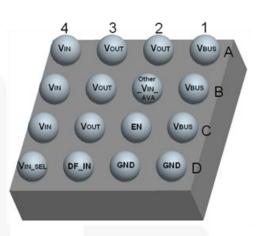


Figure 5. Pin Assignment (Bottom View)

Pin #	Name	Input / Output	Description
A1, B1, C1	V _{BUS}	Input / Output	V _{BUS} at USB: Power input / output. bi-directional switch when V _{IN_SEL} = LOW.
A4, B4, C4	V _{IN}	Input / Output	V _{IN} Supply Input: Power input / output. bi-directional switch when V _{IN_SEL} = HIGH.
A2, A3, B3, C3	V _{OUT}	Input / Output	Switch Output: Power input / output.
C2	EN	Input	Enable : Active HIGH. EN voltage $\ge 2.5 \text{ V}$ can power internal circuit when V _{IN} and V _{BUS} are absent. 1 M Ω pull-down resistor is included.
D4	V _{IN_SEL}	Input / Output	Supply Selector & Status: Input power source selection input and status output. This signal is ignored during EN=LOW.Selector input during EN=HIGH: HIGH = switch V_{IN} to V_{OUT} / LOW = switch V_{BUS} to V_{OUT} .Status output during EN=LOW: HIGH = V_{IN} is used for V_{OUT} / LOW = V_{BUS} is used for V_{OUT} .
D3	DF_IN	Input	Default Supply Selector during EN=LOW : Input. Floating = VBUS connects to V_{OUT} . LOW means V_{IN} connects to V_{OUT} . This signal is ignored during EN=HIGH. 1 µA pull-up current source is included.
B2	$Other_V_{\text{IN}_\text{AVA}}$	Output	Other Supply Input Status: Open-drain output. HI-Z = both V_{IN} and V_{BUS} are valid. LOW = the other power source is not valid.
D1, D2	GND		Ground

Pin Description

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Table	Table 1. Truth Table							
EN	V _{IN} >UVLO	V _{BUS} >UVLO	V_{IN_SEL}	DF_IN	Other_V _{IN_AVA}	V _{OUT}	Comment	
HIGH	x	х	LOW	х	HI-Z if V _{IN} & V _{BUS} >UVLO LOW if V _{IN} or V _{BUS} <uvlo< td=""><td>V_{BUS}</td><td>V_{OUT} is selected by V_{IN_SEL}</td></uvlo<>	V _{BUS}	V _{OUT} is selected by V _{IN_SEL}	
HIGH	x	х	HIGH	х	HI-Z if V _{IN} & V _{BUS} >UVLO LOW if V _{IN} or V _{BUS} <uvlo< td=""><td>V_{IN}</td><td>Bi-directional channel</td></uvlo<>	V _{IN}	Bi-directional channel	
LOW	YES	NO	HIGH	Х	LOW	V _{IN}	Automatic selection to	
LOW	NO	YES	LOW	х	LOW	V _{BUS}	valid input V _{IN_SEL} is output.	
LOW	YES	YES	LOW	Floating	HIGH	V _{BUS}	V _{OUT} is selected by	
LOW	YES	YES	HIGH	LOW	HIGH	V _{IN}	DF_IN V _{IN_SEL} is output.	
LOW	NO	NO	Х	Х	LOW	Floating	OFF	
Notes			-					

Notes:

1. Internal pull-down at EN.

2. 1 µA pull-up current source at DF_IN.

Absolute Maximum Ratings

Stresses exceeding the Absolute Maximum Ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters				Max.	Unit
		Continuous		-1.4	10	
V _{PIN}	V _{IN} , V _{BUS} to GND	Pulsed, 100 ms I	Maximum Non-Repetitive	-2.0	18	v
	V _{OUT} to GND ⁽³⁾			-0.3	16.0	v
	EN, DF_IN, V _{IN_SEL} , Other_V _{IN_AVA} to GND			-0.3	6.0	
I _{SW}	Maximum Continuous Sv	m Continuous Switch Current per Channel			2	A
t _{PD}	Total Power Dissipation a	tal Power Dissipation at T _A =25°C			2.25	W
TJ	Operating Junction Temp	ating Junction Temperature				°C
T _{STG}	Storage Junction Temper	Junction Temperature			+150	°C
Θ_{JA}	Thermal Resistance, Jun	mal Resistance, Junction-to-Ambient (1in. Square Pad of 2 oz. Copper)			55 ⁽⁴⁾	°C/W
		Human Body Mo	del, JESD22-A114	3		
ESD	Electrostatic Discharge	Charged Device	Model, JESD22-C101	1.5		kV
ESD	Capability	IEC61000-4-2	Air Discharge (VIN, VBUS to GND)	15		_ ĸv
		System Level ⁽⁵⁾	Contact Discharge (VIN, VBUS to GND)	8]

Notes:

- 3. If external voltage of more than 10.5 V is applied to V_{OUT}, the slew rate should be less than 1 V/ms from 10.5 V.
- 4. Measured using 2S2P JEDEC standard PCB.
- 5. System level ESD can be guaranteed by design.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameters	Min.	Max.	Unit
V	V _{IN}	4.0	10.5	V
V _{PIN}	V _{BUS}	4.0	6.5	v
T _A	Ambient Operating Temperature	-40	+85	°C

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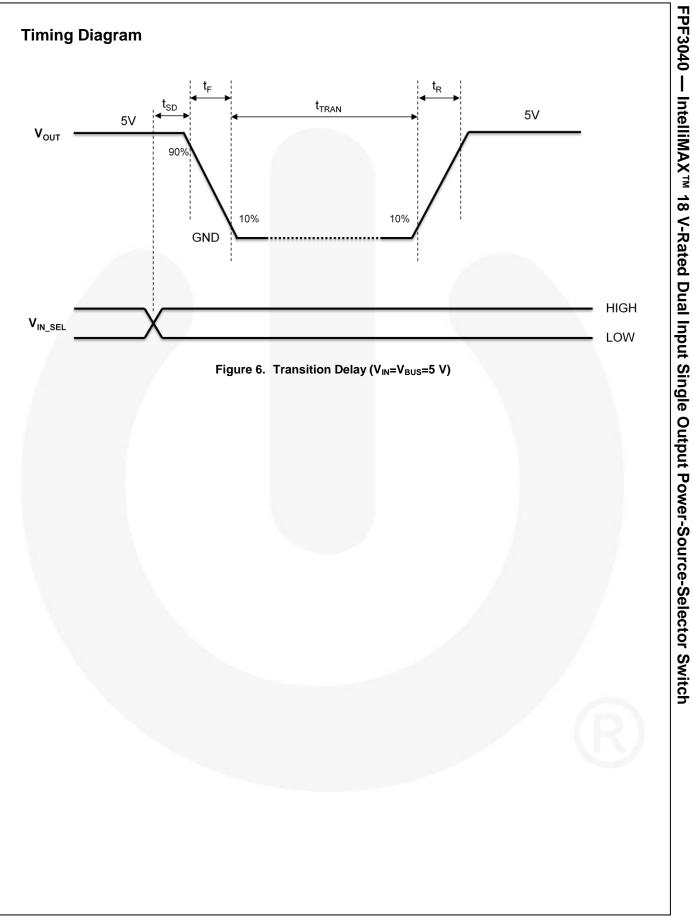
Electrical Characteristics

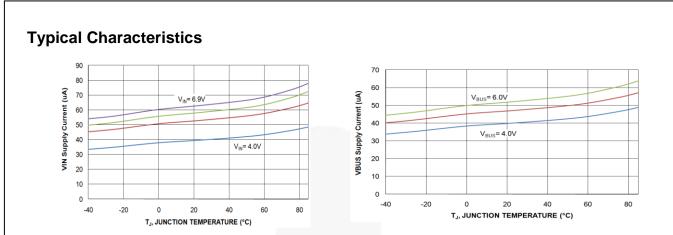
 $V_{\text{IN}}\text{=}4$ to 10.5 V, $V_{\text{BUS}}\text{=}4$ to 6.5 V, $T_{\text{A}}\text{=}\text{-}40$ to 85°C unless otherwise noted. Typical values are at $V_{\text{IN}}\text{=}V_{\text{BUS}}\text{=}5$ V, EN=HIGH and $T_{\text{A}}\text{=}25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameters	Condition	Min.	Тур.	Max.	Unit	
Basic Op	eration				•		
V _{IN}			4.0		10.5	V	
V _{BUS}	Input Voltage		4.0		6.5	V	
	Ouissant Quart	$I_{OUT}=0$ mA, EN=HIGH, V _{IN} or V _{BUS} =5 V		55	120	μA	
Ι _Q	Quiescent Current	$I_{OUT}=0$ mA, EN=5 V, V_{IN} and $V_{BUS}=GND$		33	70	μA	
		V _{IN} =8 V, I _{OUT} =200 mA, T _A =25°C		95			
	On Resistance for V _{IN}	$V_{IN}=5 V$, $I_{OUT}=200 mA$, $T_A=25^{\circ}C$		95	150	mΩ	
_		V _{IN} =5 V, I _{OUT} =200 mA, T _A =25°C to 85°C ⁽⁶⁾			200	11122	
R _{ON}		V _{BUS} =6 V, I _{OUT} =200 mA, T _A =25°C		70			
	On Resistance for V _{BUS}	V _{BUS} =5 V, I _{OUT} =200 mA, T _A =25°C		70	100	mΩ	
		V _{BUS} =5 V, I _{OUT} =200 mA, T _A =25°C to 85°C ⁽⁶⁾			140	11122	
VIH	Input Logic High Voltage	V _{IN} =4 V~10.5 V, V _{BUS} =4 V ~ 6.5 V	1.15			V	
VIL	Input Logic Low Voltage	V _{IN} =4 V~10.5 V, V _{BUS} =4 V ~ 6.5 V			0.52	V	
V _{EN(OTG)}	EN Voltage in OTG Mode ⁽⁶⁾	VIN & VBUS=Float or VIN & VBUS <vuvlo< td=""><td>2.5</td><td></td><td></td><td>V</td></vuvlo<>	2.5			V	
$R_{\text{EN}_{\text{PD}}}$	Pull-Down Resistance at EN		707	1000	1360	kΩ	
Protectio	n						
M	Under-Voltage Lockout	V _{IN} or V _{BUS} Rising	3.05	3.50	4.00	V	
V _{UVLO}	Threshold	V _{IN} or V _{BUS} Falling	2.55	3.00	3.55	V	
VUVHYS	Under-Voltage Lockout Hysteresis			0.5		V	
		VIN Rising Threshold	10.85	12.00	13.45	V	
M	Over-Voltage Lockout Threshold	V _{IN} Falling Threshold	1.1	11.5		V	
V _{OVLO}		V _{BUS} Rising Threshold	6.52	7.50	8.32	V	
		V _{BUS} Falling Threshold		7		V	
V	Over-Voltage Lockout	V _{IN}		0.5		V	
V _{OVHYS}	Hysteresis	V _{BUS}		0.5		V	
T_{SDN}	Thermal Shutdown Threshold			150		°C	
T _{SDNHYS}	Thermal Shutdown Hysteresis			20		°C	
Reverse	Current Blocking				1		
I _{RCB}	VIN or VBUS Current During RCB	V _{OUT} =8 V, V _{IN} or V _{BUS} =GND	1		30	μA	
Dynamic	Characteristics					2	
	V_{OUT} Rise Time, $V_{BUS}^{(6,7)}$			90			
t _R	V _{OUT} Rise Time, V _{IN} ^(6,7)			50		μs	
t _F	V _{OUT} Fall Time ^(6,7)	V _{IN} =V _{BUS} =5 V, R _L =150 Ω, C _L =4.7 μF, T _A =25°C		1.4		ms	
t _{TRAN}	Transition Delay ^(6,7)	1 _A -23 C	50	100		ms	
t _{SD}	Selection Delay ^(6,7)			50		μs	

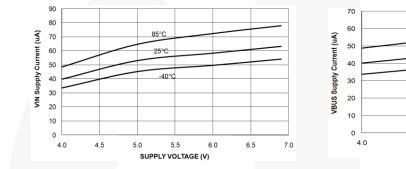
6. This parameter is guaranteed by characterization and/or design; not production tested.

7. $t_{SD}/t_{TRAN}/t_R/t_F$ are defined in Figure 6.









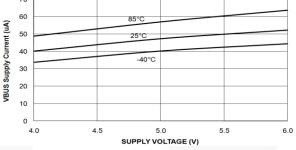
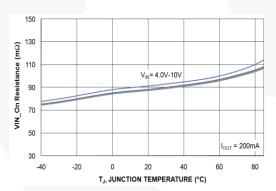


Figure 10. V_{BUS} Quiescent Current vs. Supply Voltage

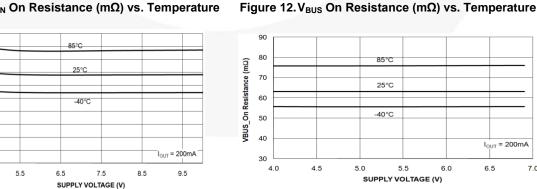
V_{Bus} = 4.0V-6.9V

TJ, JUNCTION TEMPERATURE (°C)

Figure 9. VIN Quiescent Current vs. Supply Voltage







(J)

-40

-20

VBUS_On Resistance

Figure 13.V_{IN} On Resistance (mΩ) vs. Supply Voltage Figure 14.V_{BUS} On Resistance (mΩ) vs. Supply Voltage

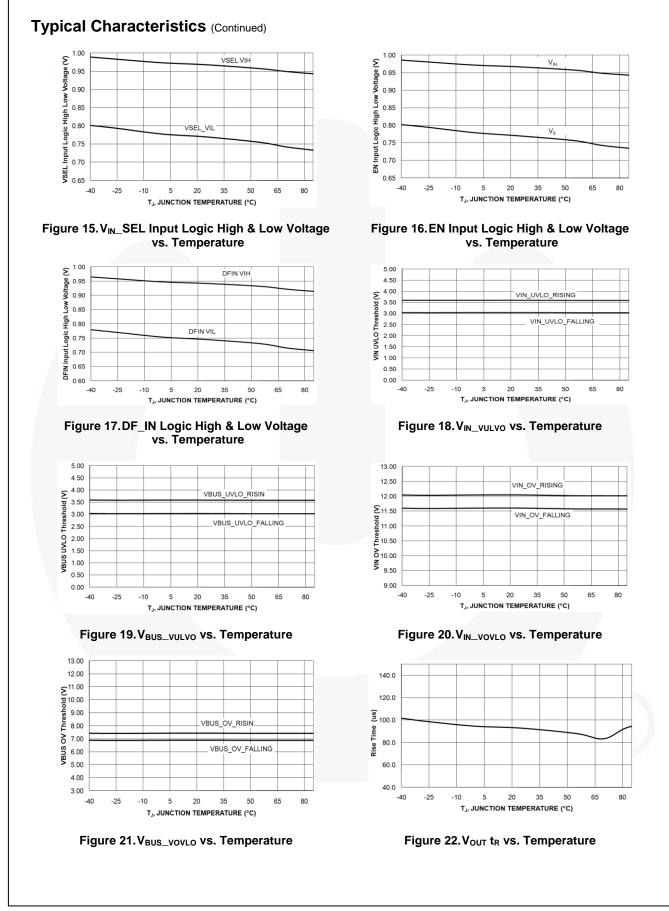
FPF3040 — IntelliMAX[™] 18 V-Rated Dual Input Single Output Power-Source-Selector Switch

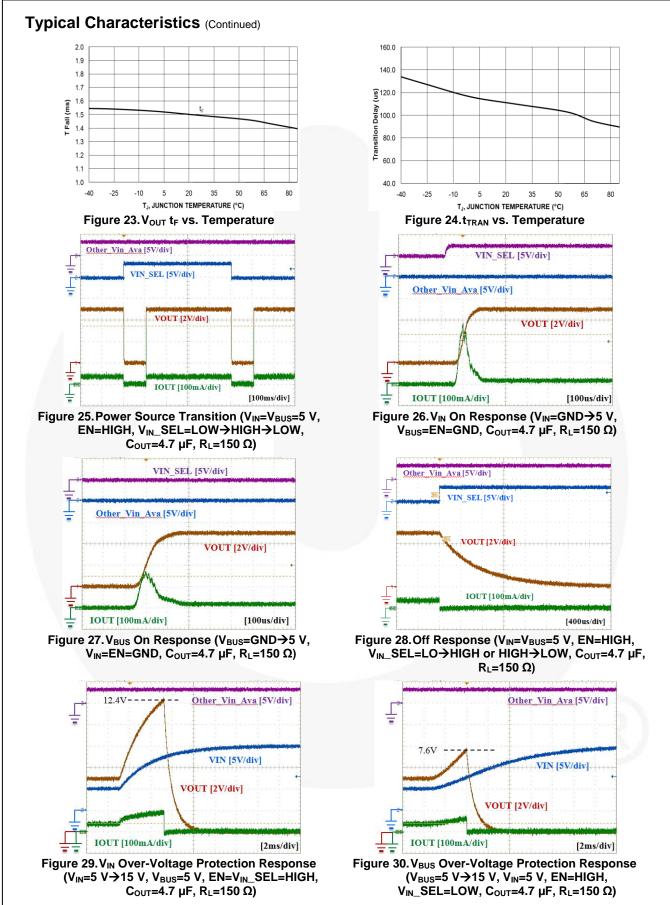
4.5

VIN On Resistance (m^Ω)

7.0

I_{OUT} = 200mA





Operation and Application Information

The FPF3040 is a 18 V, 2 A-rated, Dual-Input Single-Output (DISO) load switch with slew-rate-controlled, low-on-resistance, based-on-N-channel MOSFET. The input operating range is from 4 V to 6.5 V at V_{BUS} and from 4 V to 10.5 V at V_{IN}. The internal circuitry is powered from the highest voltage source among V_{IN}, V_{BUS}, and V_{EN}.

Input Power Source Selection

Input power source can be selected by V_{IN_SEL} and DF_IN, respectively, depending on EN state. When EN is HIGH, the input source is selected by V_{IN_SEL} regardless of DF_IN. If V_{IN_SEL} is LOW, V_{BUS} is selected. If V_{IN_SEL} is HIGH, V_{IN} is selected.

Table 2. Input Power Selection	by VIN	SEL
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EN	V _{IN} >UVLO	V _{BUS} >UVLO	V_{IN_SEL}	DF_IN	\mathbf{V}_{OUT}
HIGH	Х	Х	LOW	х	V_{BUS}
HIGH	Х	Х	HIGH	Х	V_{IN}

When EN is LOW, the input source is selected by DF_IN and the number of valid input sources. If only one input source is valid, or more than UVLO, the source is selected automatically, regardless of DF_IN, to make a charging path in case the battery is depleted. If both V_{BUS} and V_{IN} have valid input sources, the input source is selected by DF_IN. If DF_IN is LOW, V_{IN} is selected. If DF_IN is HIGH or floating, V_{BUS} is selected. DF_IN is biased HIGH with an internal 1 μ A pull-up current source.

Table 3. Input Power Selection by DF_IN

EN	V _{IN} >UVLO	V _{BUS} >UVLO	V_{IN_SEL}	DF_IN	\mathbf{V}_{OUT}
LOW	YES	NO	HIGH	Х	V _{IN}
LOW	NO	YES	LOW	Х	V_{BUS}
LOW	YES	YES	LOW	Floating	V_{BUS}
LOW	YES	YES	HIGH	LOW	V _{IN}
LOW	NO	NO	Х	Х	Floating

 V_{IN_SEL} can be the status output to indicate which input power source is used during EN is LOW. If V_{IN} is used, V_{IN_SEL} shows high. If V_{BUS} is used, V_{IN_SEL} shows LOW. The voltage level of HIGH signal is 5.3 V if any one of

 $V_{\text{IN}},~V_{\text{BUS}}$ or EN is higher than 5.3 V. The signal is highest voltage among $V_{\text{IN}},~V_{\text{BUS}},$ and V_{EN} if none of them is higher than 5.3 V.

EN Voltage for Control Logic Power Supply

Internal control logic is powered from the highest voltage among V_{IN}, V_{BUS}, and V_{EN}. If valid V_{IN} or V_{BUS} higher than UVLO is applied, ON/OFF control by EN should be accomplished with V_{IH}/V_{IL}. If EN powers the internal control block without valid V_{IN} and V_{BUS}, more than 2.5 V is required on the EN pin to operate properly.

Over-Voltage Protection (OVP)

FPF3040 has over-voltage protection at both V_{IN} and V_{BUS}. If V_{IN} or V_{BUS} is higher than 12 V or 7.5 V, respectively, the power switch is off until input voltage is lower than the over-voltage trip level by hysteresis voltage of 0.5 V.

Reverse Power Supply for OTG

FPF3040 has a bi-directional switch so reverse power is allowed for On-The-Go (OTG) operation. Even if both V_{IN} and V_{BUS} are not available, reverse power can be also supported if internal control circuitry is powered by EN.

Reverse-Current Blocking

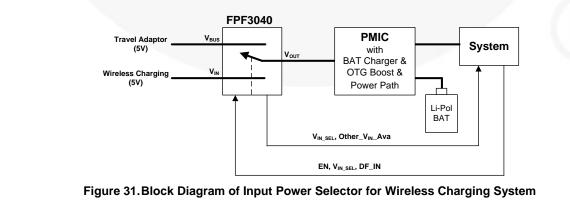
FPF3040 supports reverse-current blocking during EN LOW and an unselected channel.

Thermal Shutdown

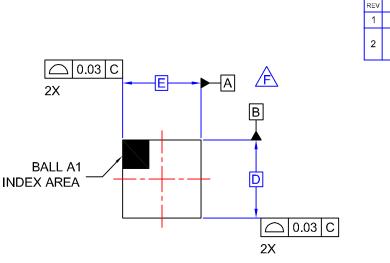
During FPF3040 thermal shutdown, the power switch is turned off if junction temperature reaches over 150°C to avoid damage.

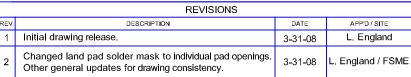
Wireless Charging System

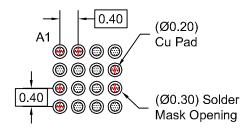
FPF3040 can be used for an input power selector supporting Travel Adaptor (TA) and Wireless Charging (WC) with a single-input-based battery charger or Power Management IC (PMIC), including a charging block as shown in Figure 31. The system can recognize an input power source change between 5 V TA and 5 V WC without detection circuitry because FPF3040 has a 100 ms transition delay. OTG Mode can be supported without an additional power path, such as a MOSFET.



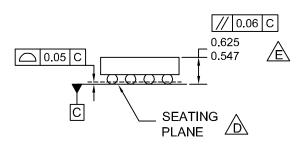
D	E	Х	Y
.96 mm ±0.03 mm	1.76 mm ±0.03 mm	0.28 mm	0.38 mm



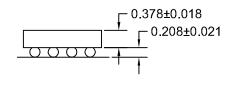




RECOMMENDED LAND PATTERN (NSMD PAD TYPE)



TOP VIEW



SIDE VIEWS

NOTES:

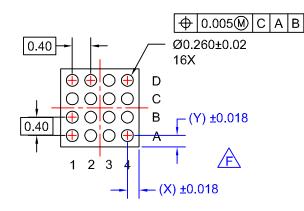
- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASME Y14.5M, 1994.
- D. DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.

<u>E</u>PACKAGE NOMINAL HEIGHT IS 586 MICRONS ±39 MICRONS (547-625 MICRONS).

F. FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.

G. DRAWING FILNAME: MKT-UC016AArev2.

APPROVALS	DATE	FAIR	<u>ен</u> ш			
L. England	10-26-09	SEMICO				
^{DFTG. CHK.} E. Shacham	10-26-09					
ENGR. CHK.		16BALL WLCSP, 4X4 ARRAY 0.4MM PITCH, 250UM BALL				
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BOTTOM VIEW



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Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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